

# **HAT2196C**

# Silicon N Channel MOS FET Power Switching

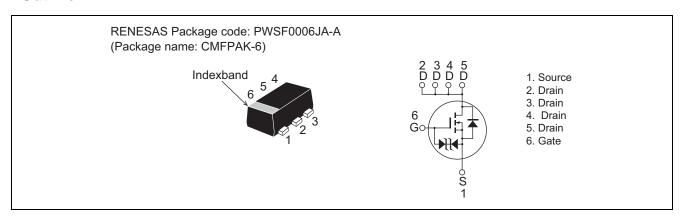
R07DS1178EJ0600 (Previous: REJ03G1235-0500)

> Rev.6.00 Mar 19, 2014

#### **Features**

- Low on-resistance  $R_{DS(on)} = 45 \text{ m}\Omega \text{ typ. (at } V_{GS} = 4.5 \text{ V})$
- Low drive current.
- High density mounting
- 2.5 V gate drive devices.

#### **Outline**



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	20	V
Gate to source voltage	$V_{GSS}$	±12	V
Drain current	I <sub>D</sub>	2.5	А
Drain peak current	I <sub>D(pulse)</sub> Note1	10	А
Body-drain diode reverse drain current	I <sub>DR</sub>	2.5	А
Channel dissipation	Pch <sup>Note 2</sup>	850	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. When using the glass epoxy board. (FR4  $40 \times 40 \times 1.6$ mm)

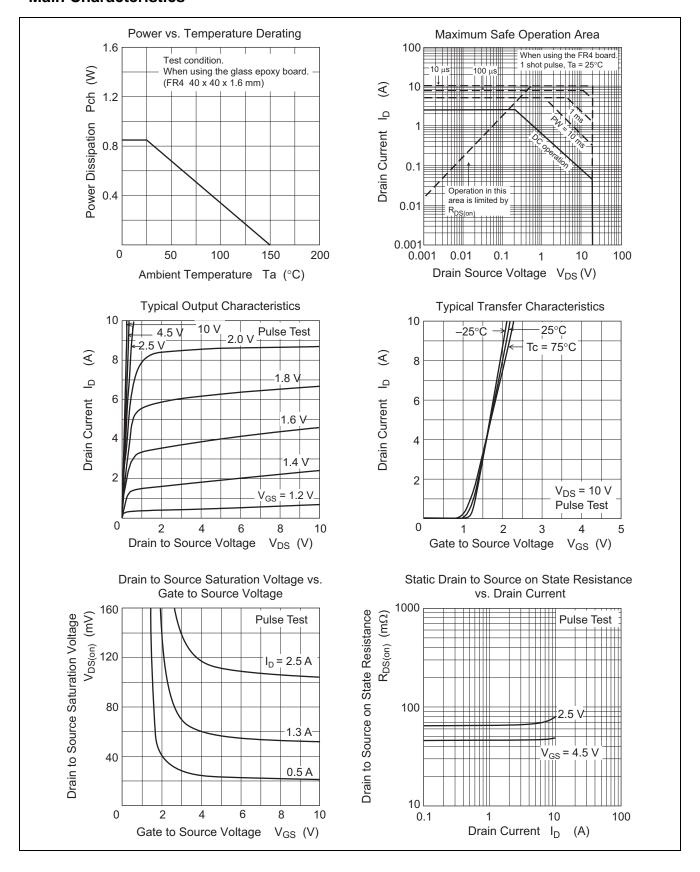
### **Electrical Characteristics**

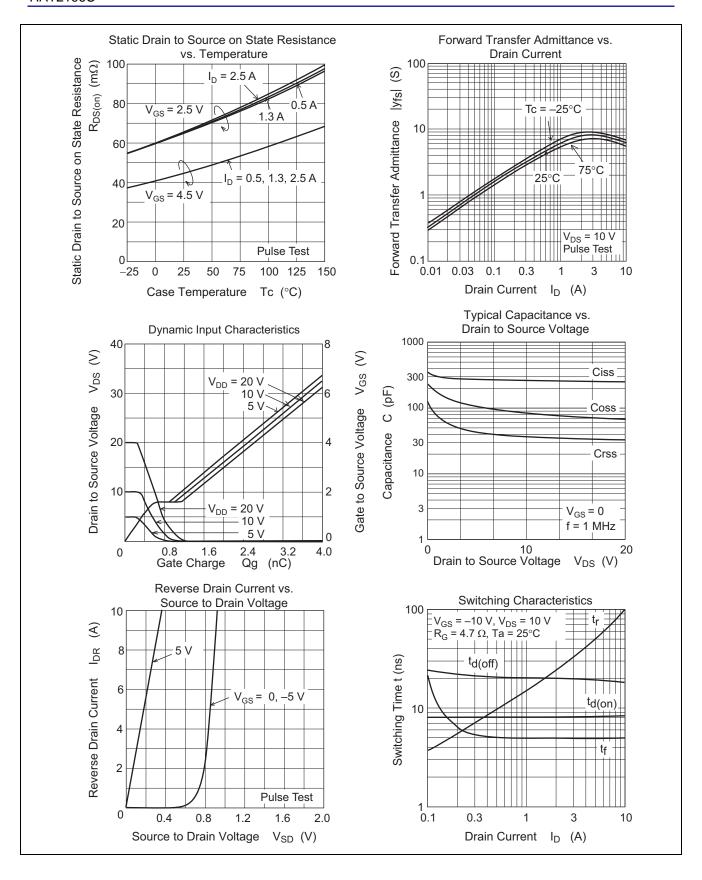
 $(Ta = 25^{\circ}C)$ 

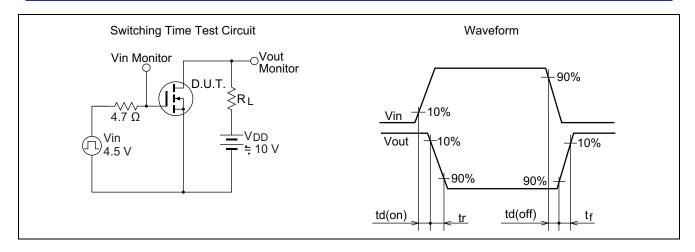
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	20	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to Source breakdown voltage	$V_{(BR)GSS}$	±12	_	_	V	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0$
Gate to Source leakage current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$
Drain to Source leakage current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 20 \text{ V}, V_{GS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	>	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Drain to Source on state resistance	R <sub>DS(on)</sub>	_	45	58	mΩ	$I_D = 1.3 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
	R <sub>DS(on)</sub>	_	66	93	mΩ	$I_D = 1.3 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y <sub>fs</sub>	4.5	7	_	S	$I_D = 1.3 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	270	_	pF	$V_{GS} = 0, f = 1 \text{ MHz},$
Output capacitance	Coss	_	85	_	pF	V <sub>DS</sub> = 10 V
Reverse transfer capacitance	Crss	_	35	_	pF	
Total gate charge	Qg	_	2.8	_	nC	$V_{GS} = 4.5 \text{ V}, V_{DS} = 10 \text{ V},$
Gate to Source charge	Qgs	_	0.6	_	nC	I <sub>D</sub> = 2.5 A
Gate to Drain charge	Qgd	_	0.5	_	nC	
Turn - on delay time	t <sub>d(on)</sub>	_	8	_	ns	$V_{GS} = 4.5 \text{ V}, I_D = 1.3 \text{ A}, \\ V_{DD} = 10 \text{ V}, \\ R_L = 7.7 \Omega , R_g = 4.7 \Omega$
Rise time	t <sub>r</sub>	_	19	_	ns	
Turn - off delay time	$t_{d(off)}$	_	20	_	ns	
Fall time	t <sub>f</sub>	_	5	_	ns	
Body - Drain diode forward voltage	$V_{DF}$	_	0.8	1.1	V	$I_F = 2.5 \text{ A}, V_{GS} = 0^{\text{Note3}}$

Notes: 3. Pulse test

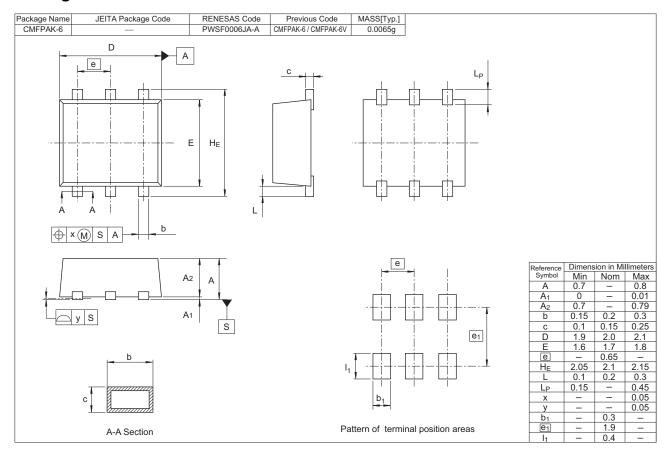
#### **Main Characteristics**







### **Package Dimensions**



## **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
HAT2196C-EL-E	3000 pcs	Taping

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